

IN THE CLAIMS

**Please amend the claims to read as shown below:<sup>2</sup>**

**Please cancel without prejudice Claims 1-20.**

**Please add the following new claims:**

21. (New) ~~A~~ single-substrate-processing apparatus, comprising:

an airtight process chamber including a casing and configured to process a target

substrate;

a worktable configured to support the target substrate within the casing of the process chamber,

a pedestal standing upright in the process chamber and connected to the worktable to support the worktable; and

a conduction structure configured to conduct static electricity generated on the worktable to a grounded portion outside the process chamber, the conduction structure having a conduction route for the static electricity including a conductive film formed on the worktable, formed on the pedestal, and electrically isolated from the casing of the chamber.

22. (New) The apparatus according to claim 21, wherein the conductive film comprises at least one of silicon carbide and titanium oxide.

23. (New) The apparatus according to claim 21, wherein the conductive film is a film formed by means of chemical vapor deposition.

24. (New) The apparatus according to claim 21, wherein the conductive film is a film formed by means of thermal spraying.

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<sup>2</sup>The changes to the claims are shown using underscoring and bracketing in the marked-up copy attached herewith.

25. (New) The apparatus according to claim 21, wherein the conductive film has a thickness ranging from 20 to 100  $\mu\text{m}$ .

26. (New) The apparatus according to claim 21, wherein the worktable and the pedestal comprise insulating surfaces on which the conductive film is formed.

27. (New) The apparatus according to claim 26, wherein the worktable and the pedestal comprise insulating materials, and portions of the worktable and the pedestal facing an atmosphere in the process chamber are covered with the conductive film.

28. (New) The apparatus according to claim 21, wherein the conduction structure is arranged such that the conductive film and a conductive portion of the casing are electrically connected to ground.

29. (New) The apparatus according to claim 21, wherein the pedestal is attached to the process chamber by a fixing member which penetrates the casing of the process chamber, and the conduction structure is arranged such that a conductive portion of the fixing member is electrically connected to the conductive film.

30. (New) The apparatus according to claim 29, further comprising:  
a bias section configured to selectively apply a positive electrical potential to the conductive portion of the fixing member.

31. (New) The apparatus according to claim 30, wherein the bias section comprises:  
a switch configured to switch between a state where the conductive portion of the fixing member is grounded and a state where the conductive portion of the fixing member is connected to the bias section.

32. (New) The apparatus according to claim 21, further comprising:  
a supply section configured to supply a process gas into the process chamber;  
an exhaust section configured to vacuum-exhaust the process chamber,

a window formed in the casing of the process chamber and facing the worktable; and  
a UV lamp disposed outside the process chamber and facing the window, the UV  
lamp being configured to radiate UV rays onto the process gas above the worktable to  
activate the process gas.

33. (New) The apparatus according to claim 32, wherein the process gas contains an  
oxidizing gas for subjecting the target substrate to oxidation.

34. (New) The apparatus according to claim 33, wherein the oxidizing gas comprises  
ozone gas.

35. (New) A single-substrate-processing apparatus, comprising:  
an airtight process chamber including a casing and configured to process a target  
substrate;  
a worktable configured to support the target substrate within the casing of the process  
chamber,  
a pedestal connected to the worktable to support the worktable; and  
a conduction structure configured to conduct static electricity generated on the  
worktable to a grounded portion outside the process chamber, the conduction structure having  
a conduction route for the static electricity including a conductive film formed on the  
worktable and the pedestal, the conduction structure being arranged such that the conductive  
film and a conductive portion of the casing are electrically connected to ground.

36. (New) The apparatus according to claim 35, wherein the conductive film  
comprises at least one of silicon carbide and titanium oxide.

37. (New) The apparatus according to claim 35, wherein the conductive film has a  
thickness ranging from 20 to 100  $\mu\text{m}$ .